

# SOD-123





# MBR0520

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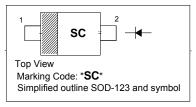
### **Surface Mount Schottky Barrier Diode**

#### **Features**

- Very low forward voltage
- High Current Capability

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RRM}$	20	V
Working Peak Reverse Voltage	$V_{RWM}$	20	V
DC Reverse Voltage	V <sub>R</sub>	20	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	0.5	А
Non-Repetitive Peak Forward Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	5.5	А
Thermal Resistance Junction to Ambient	$R_{ heta JA}$	340	°C/W
Thermal Resistance Junction to Lead	R <sub>θJL</sub>	150	°C/W
Junction Temperature	T <sub>j</sub>	- 65 to + 150	°C
Storage Temperature	T <sub>stg</sub>	- 65 to + 150	°C

<sup>1)</sup> Following any rated load condition and with rated VRRM applied.

#### Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1$ A, $T_j = 25$ °C at $I_F = 0.5$ A, $T_j = 25$ °C at $I_F = 0.1$ A, $T_j = 100$ °C at $I_F = 0.5$ A, $T_j = 100$ °C	V <sub>F</sub>	0.375 0.44 0.26 0.36	V
Reverse Current at $V_R = 10 \text{ V}$ , $T_j = 25 \text{ °C}$ at $V_R = 20 \text{ V}$ , $T_j = 25 \text{ °C}$ at $V_R = 10 \text{ V}$ , $T_j = 100 \text{ °C}$ at $V_R = 20 \text{ V}$ , $T_j = 100 \text{ °C}$	I <sub>R</sub>	40 150 3 7	μΑ μΑ mA mA
Total Capacitance at $V_R$ = 5 V (test signal range 100 KHz to 1 MHz), $T_j$ = 25 °C	C <sub>tot</sub>	110	pF



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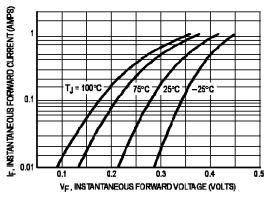


Figure 1. Typical Forward Voltage

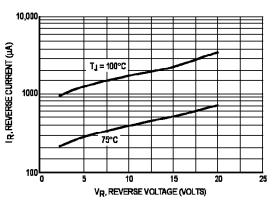


Figure 2. Typical Reverse Current

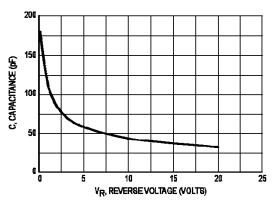


Figure 3. Typical Capacitance

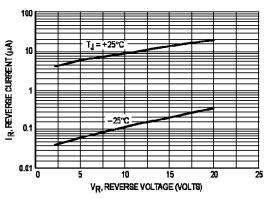


Figure 4. Typical Reverse Current

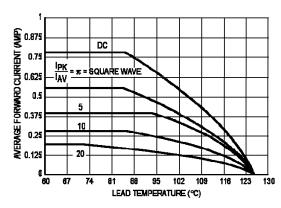


Figure 5. Current Derating (Lead)

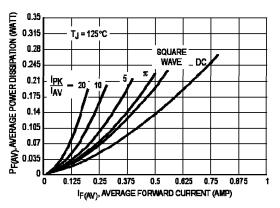


Figure 6. Power Dissipation